

FIG. 1

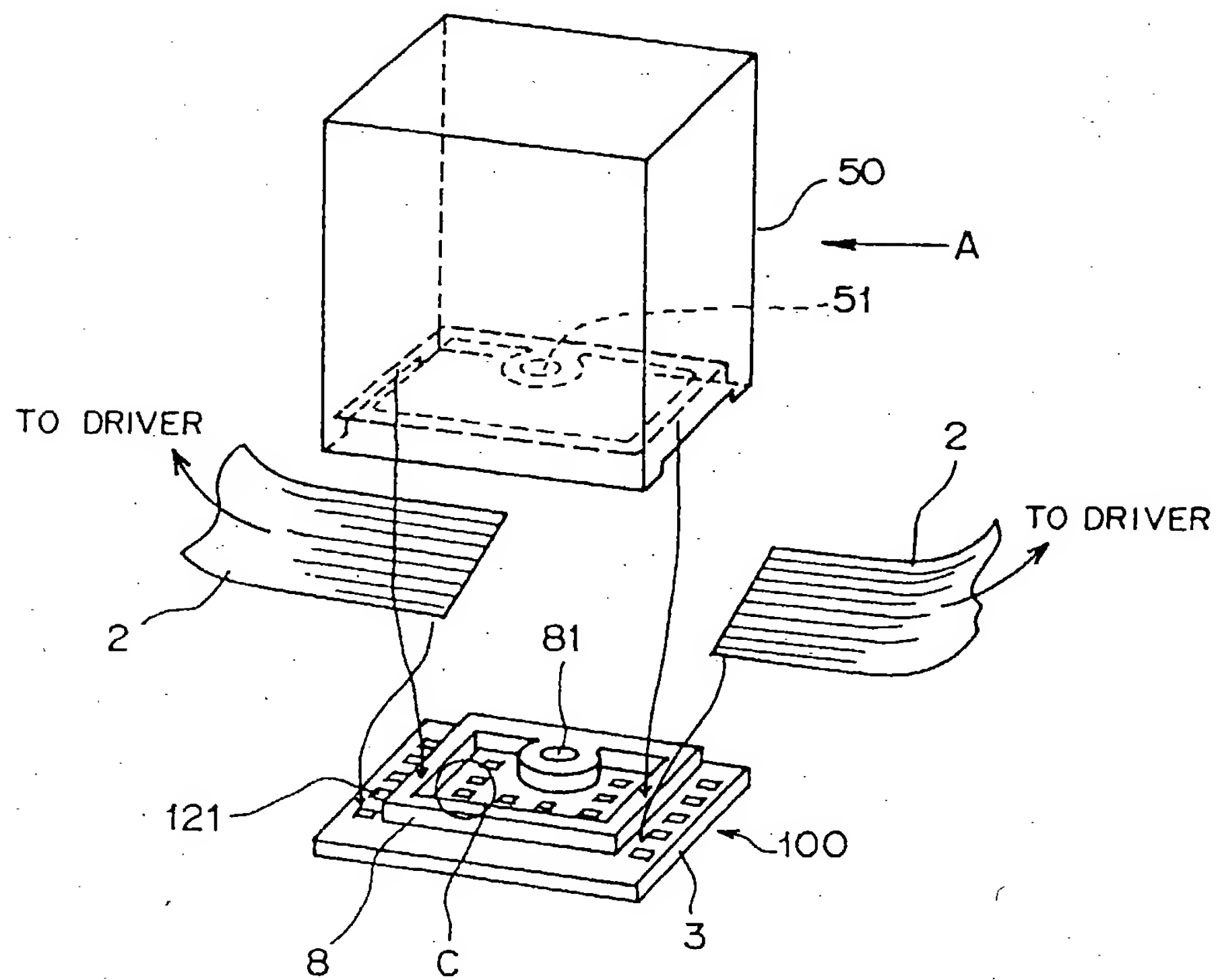


FIG. 2

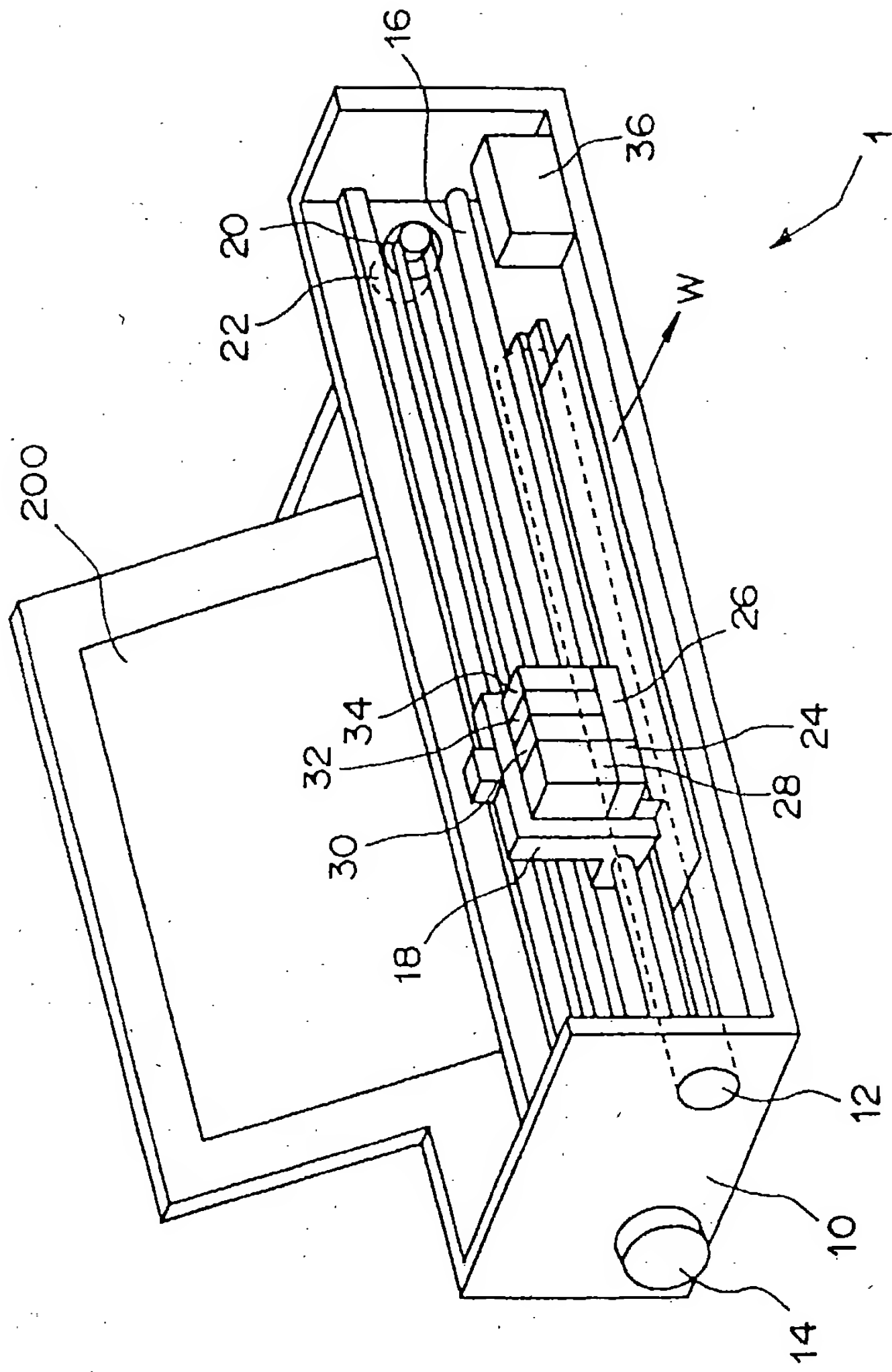
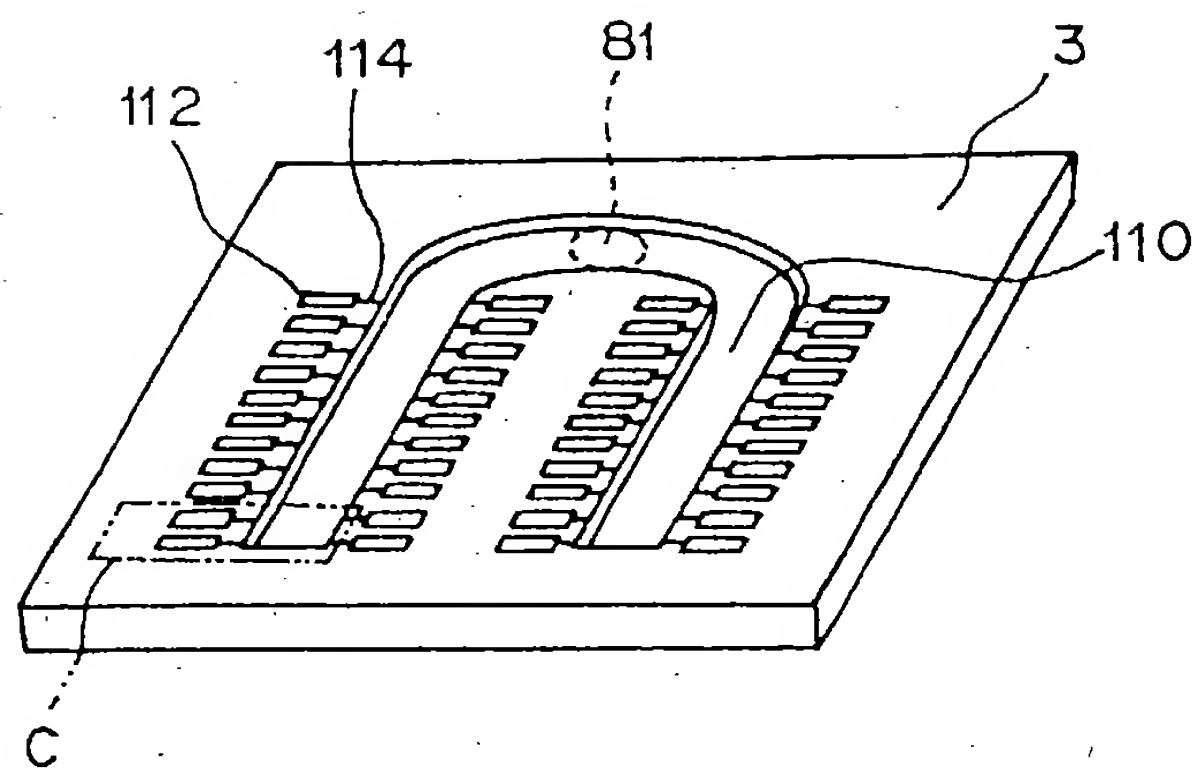
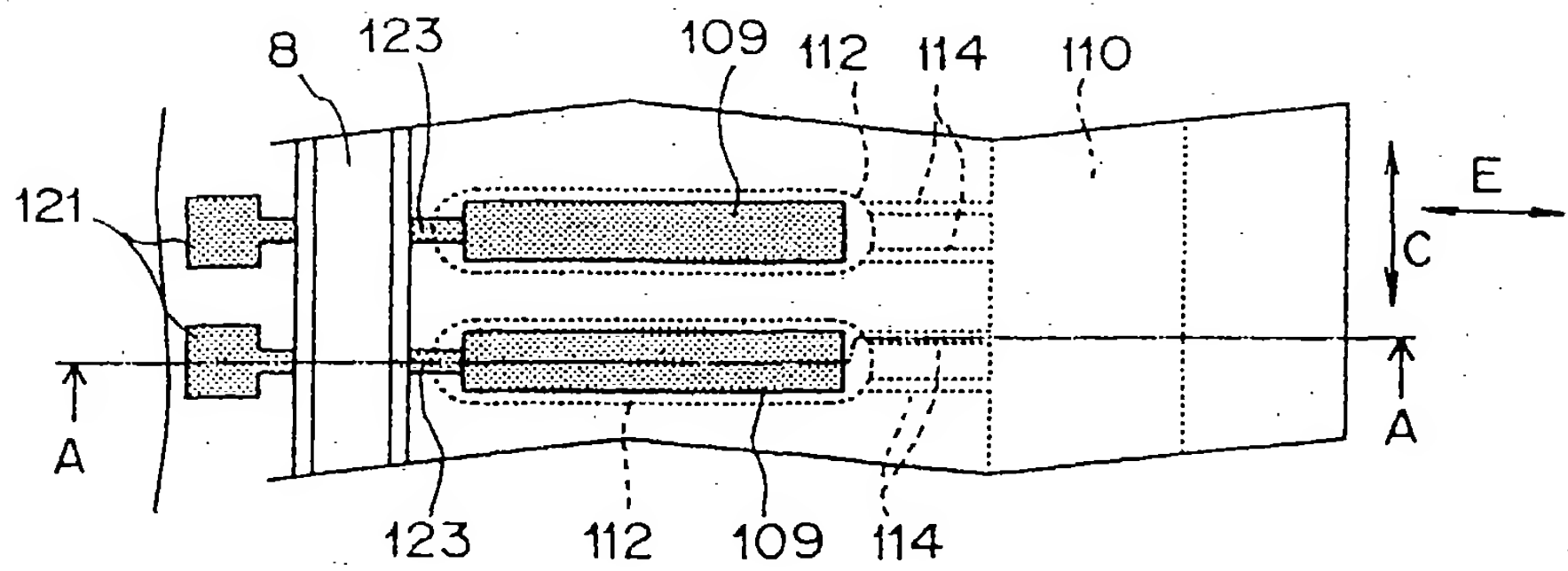


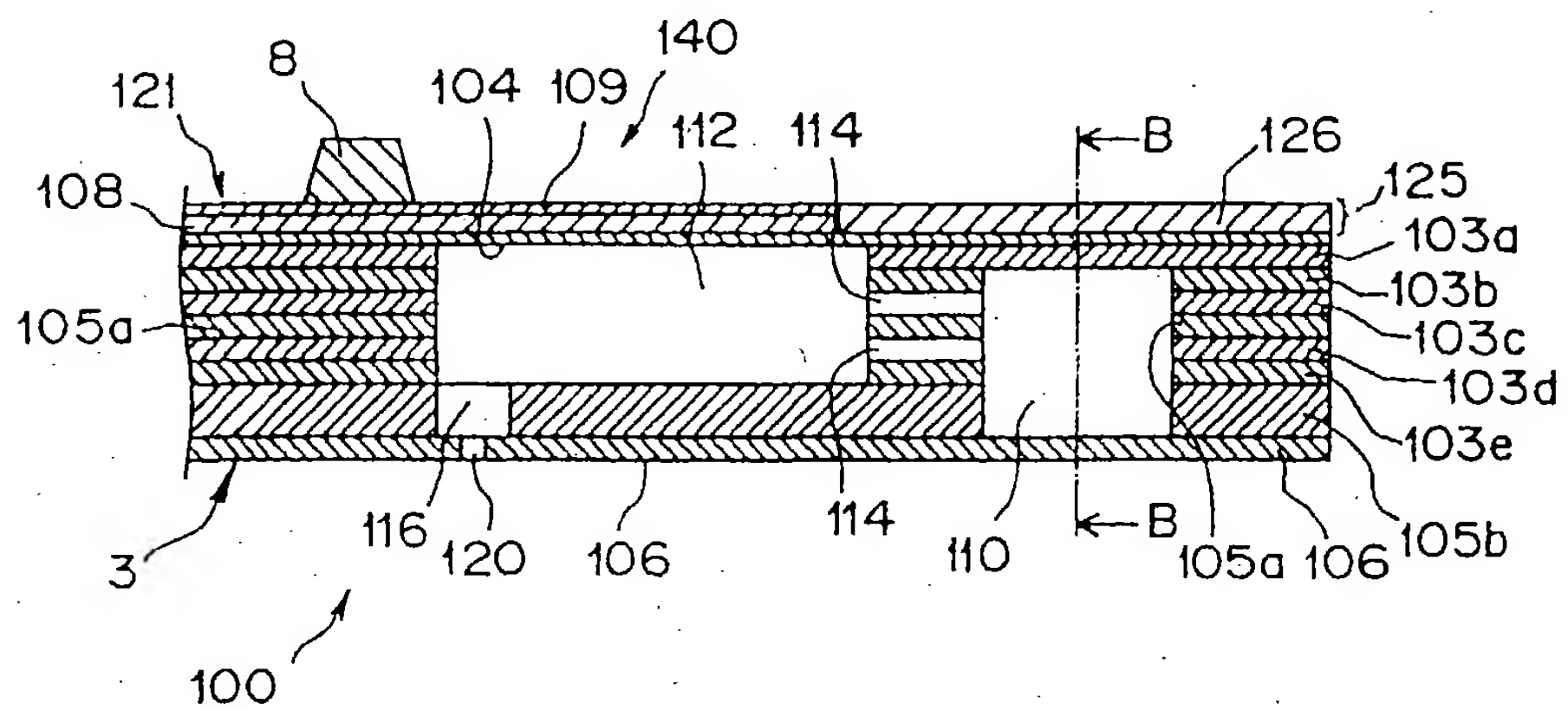
FIG. 3



# FIG. 4



# FIG. 5



# FIG. 6

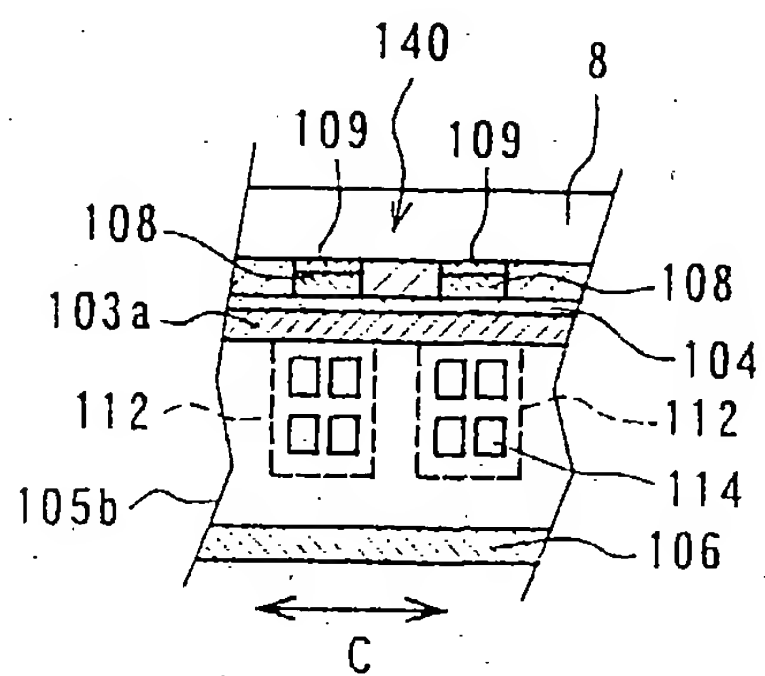


FIG. 7

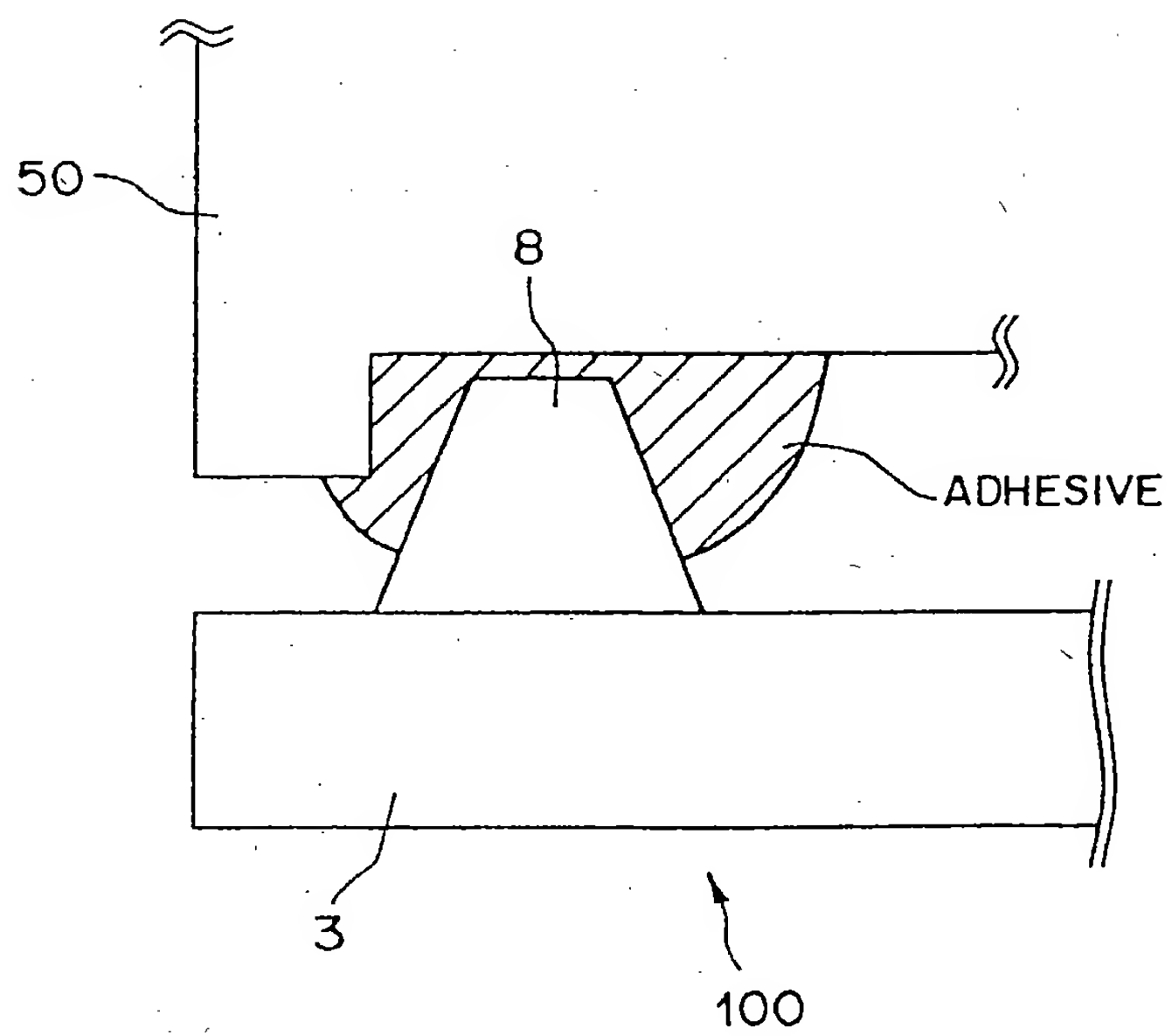


FIG. 8

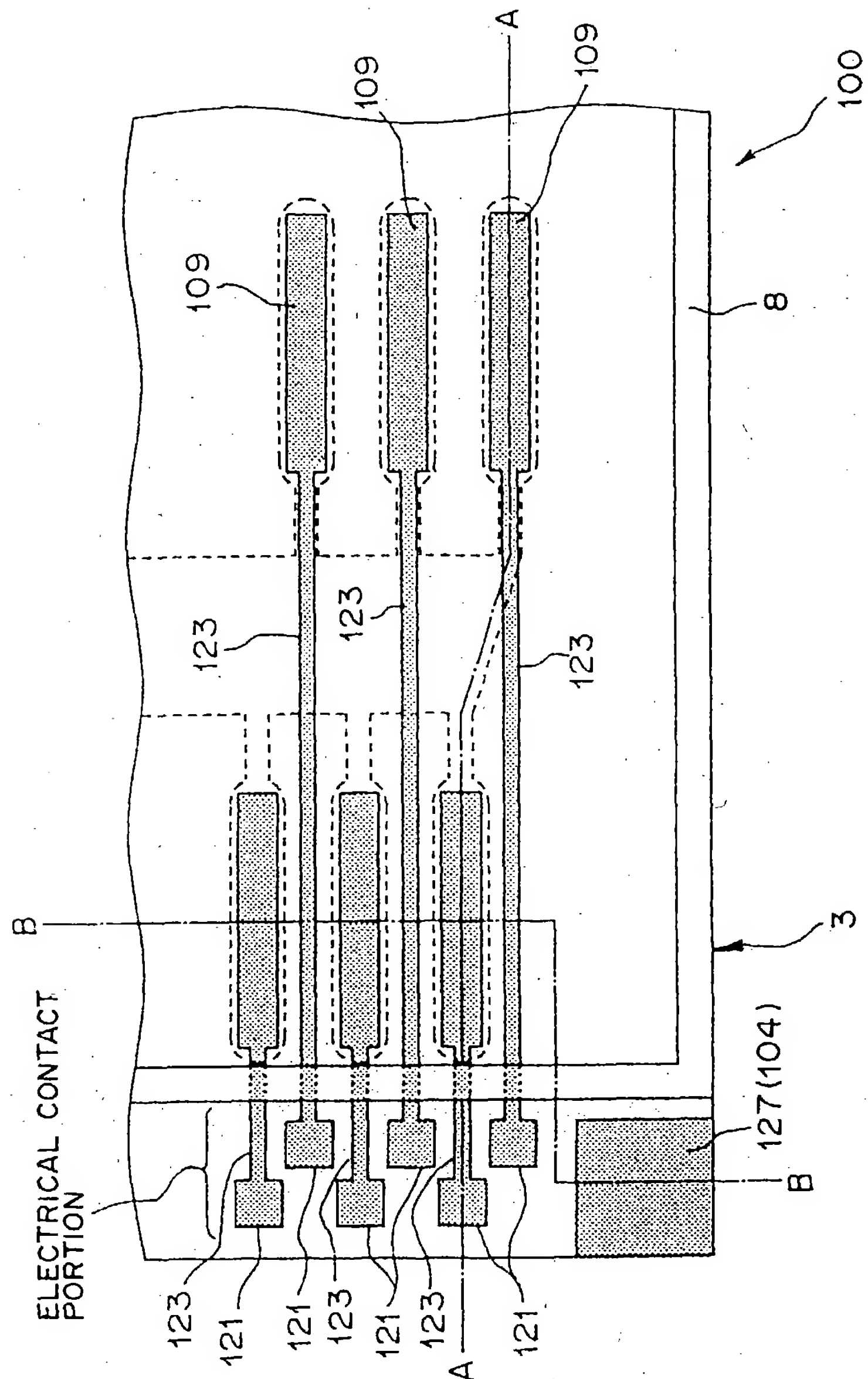


FIG. 9

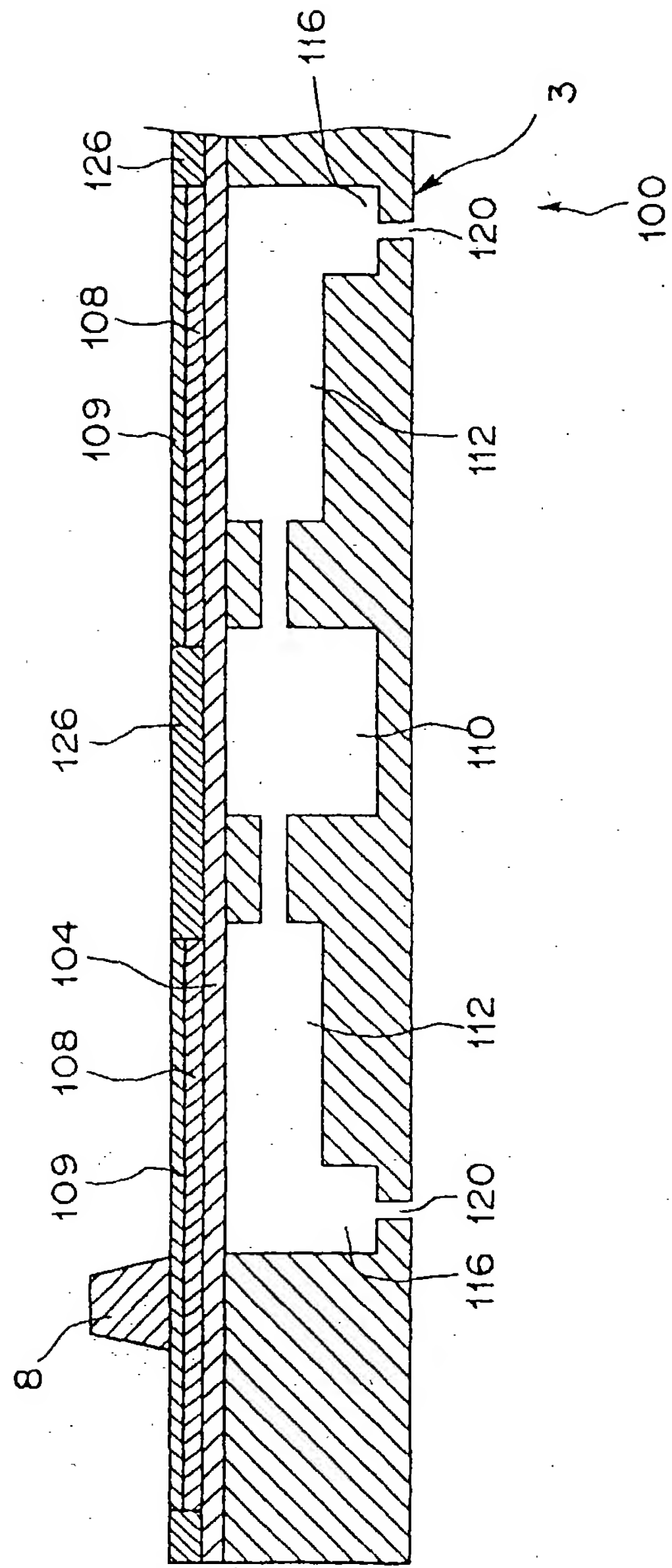


FIG. 10

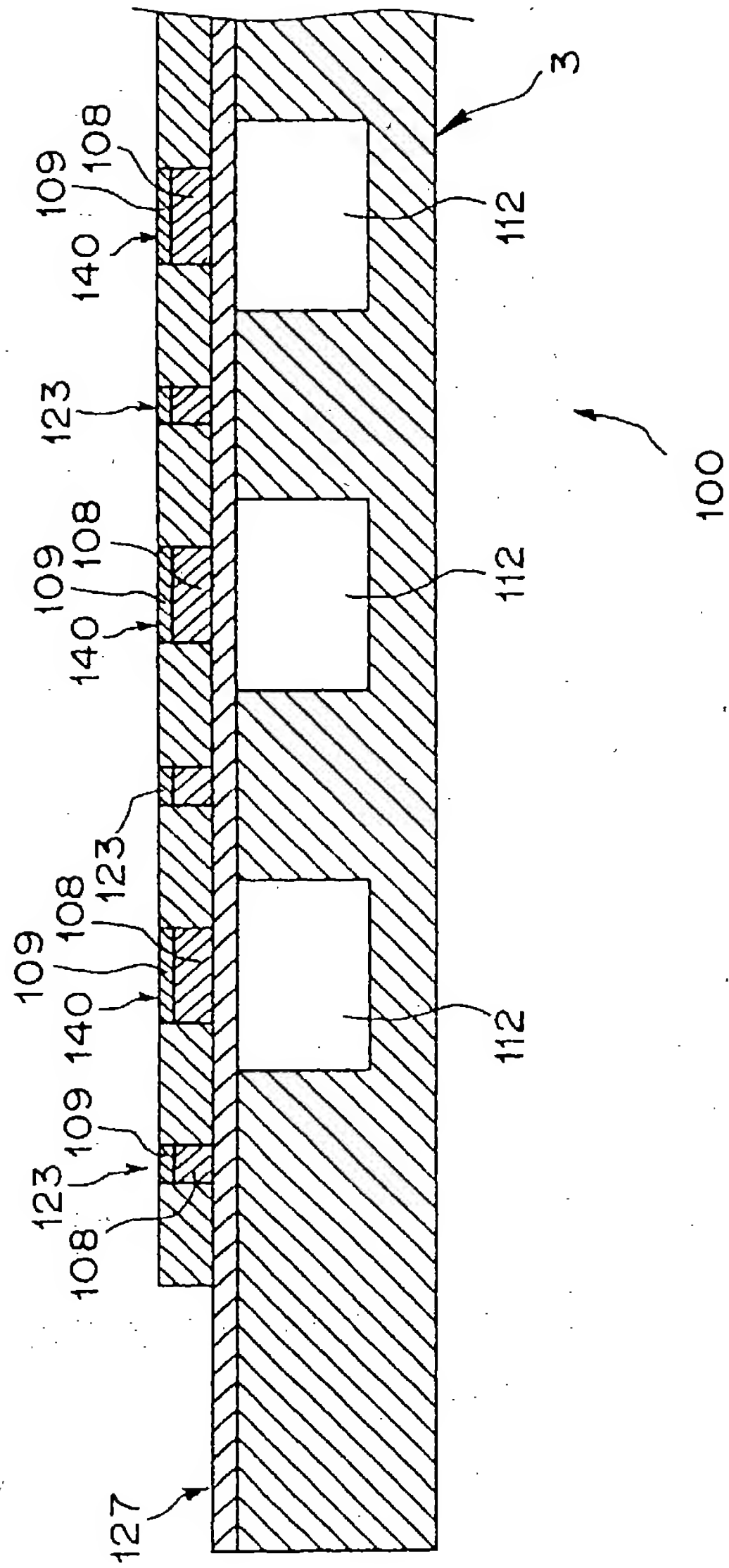




FIG. 11(A)

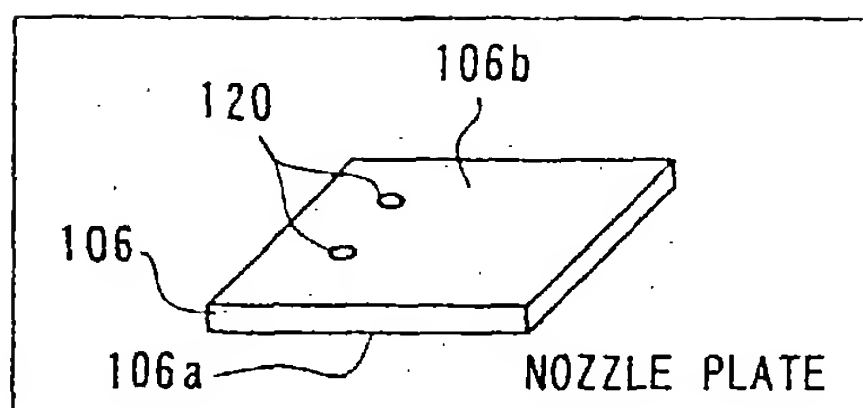


FIG. 11(B)

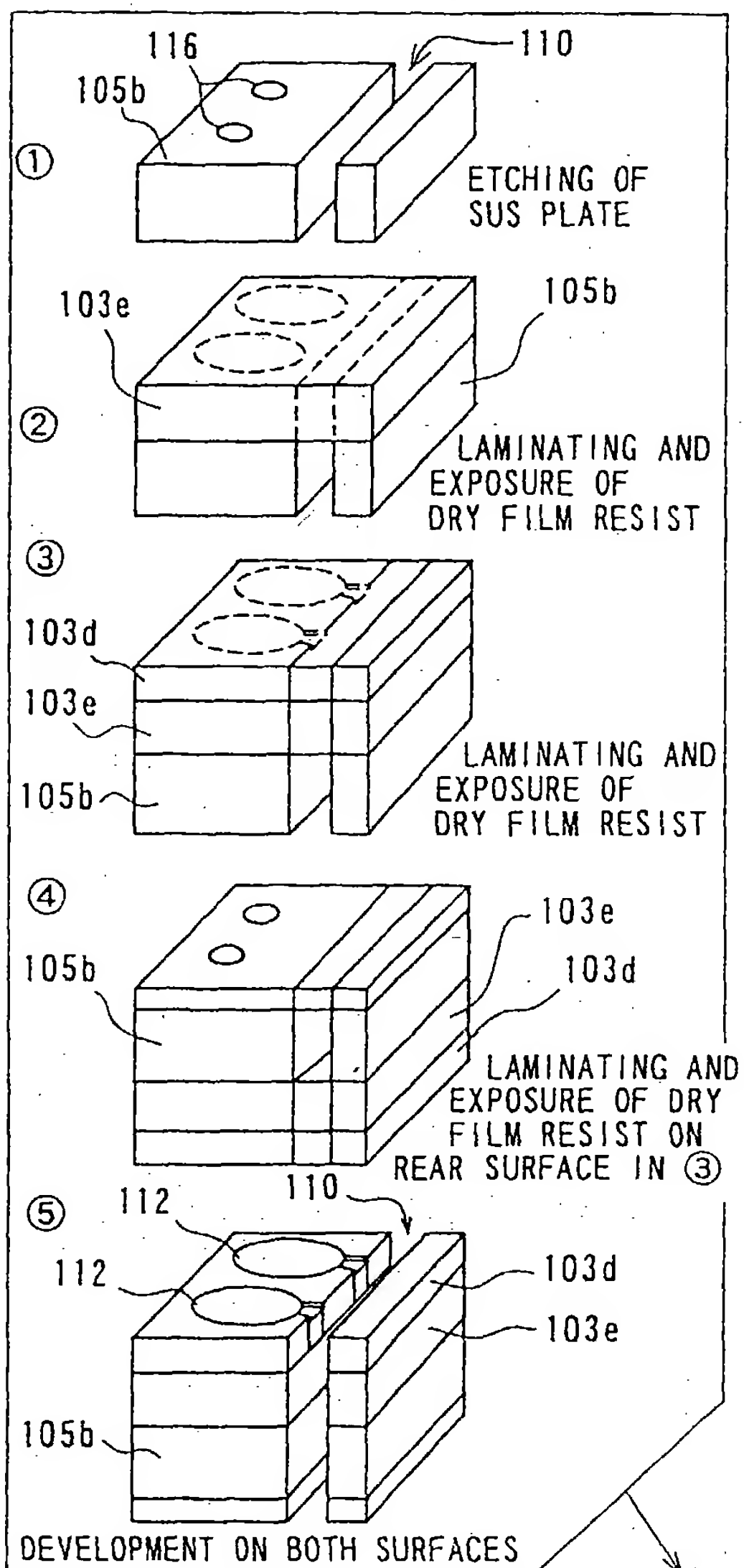


FIG. 11(D)

MgO FRAME

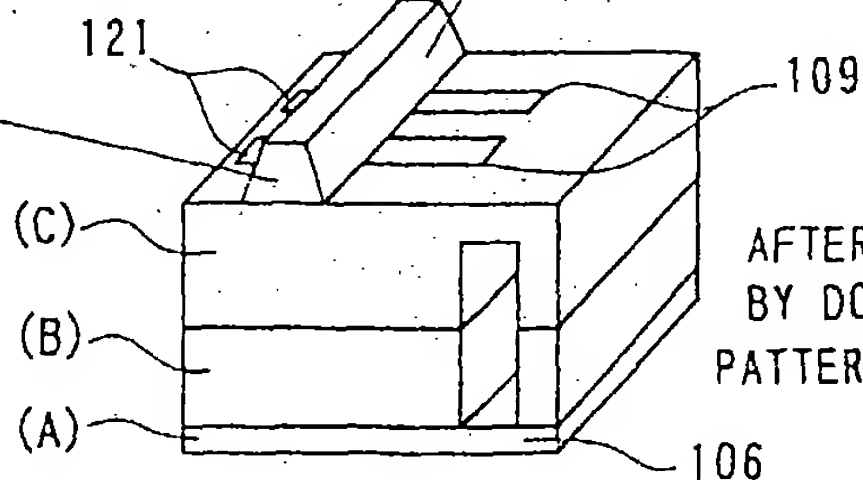
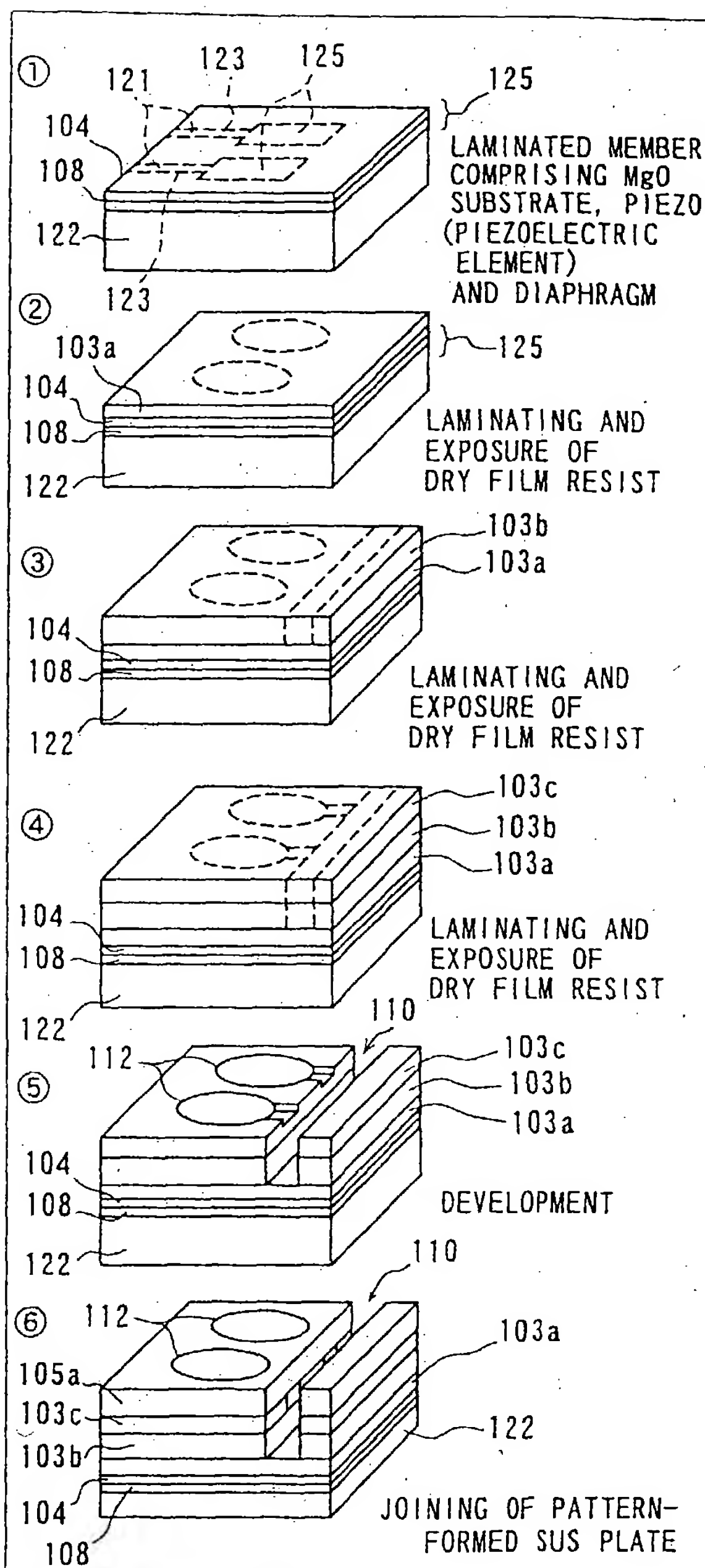


FIG. 11(C)



AFTER INTEGRATION OF (A)+(B)+(C)  
BY DOUBLE-JOINING AND CURING,  
PATTERNING REMOVAL OF MgO SUBSTRATE

FIG. 12

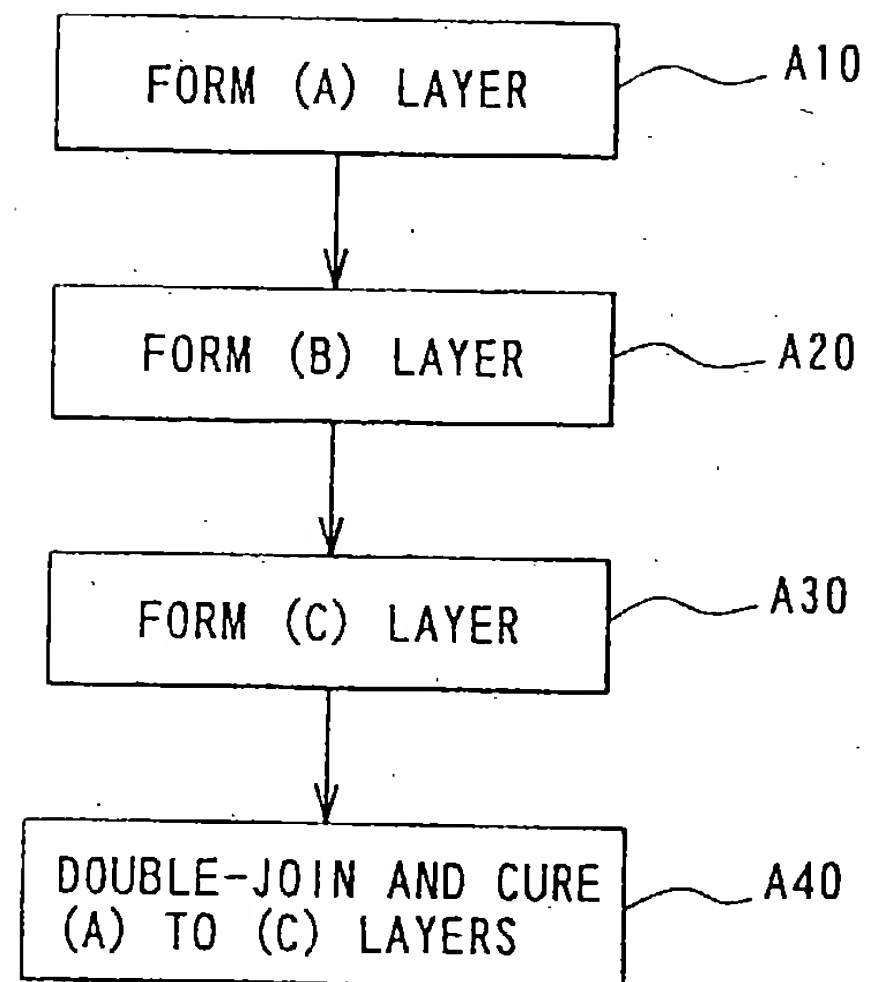


FIG. 13

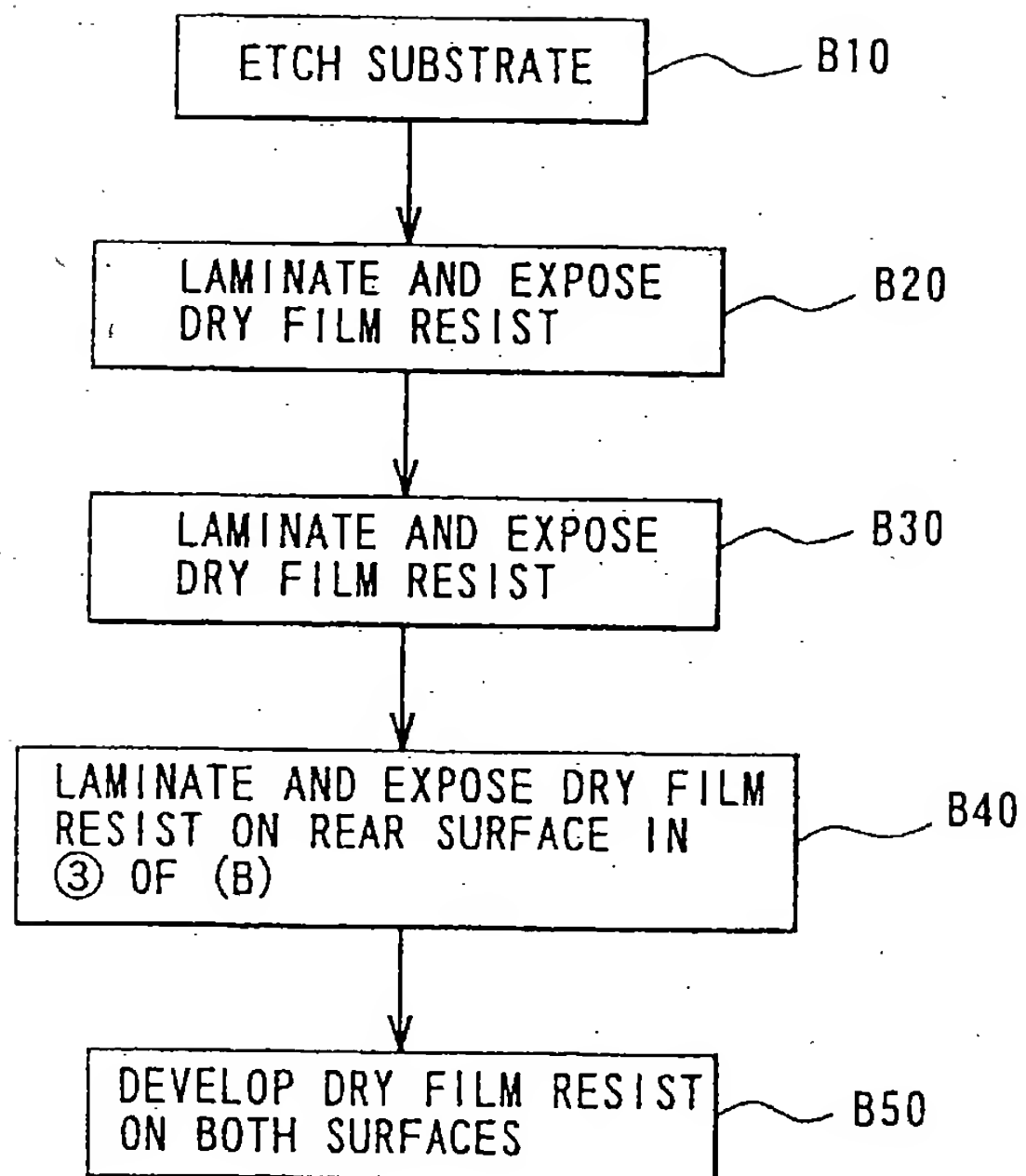
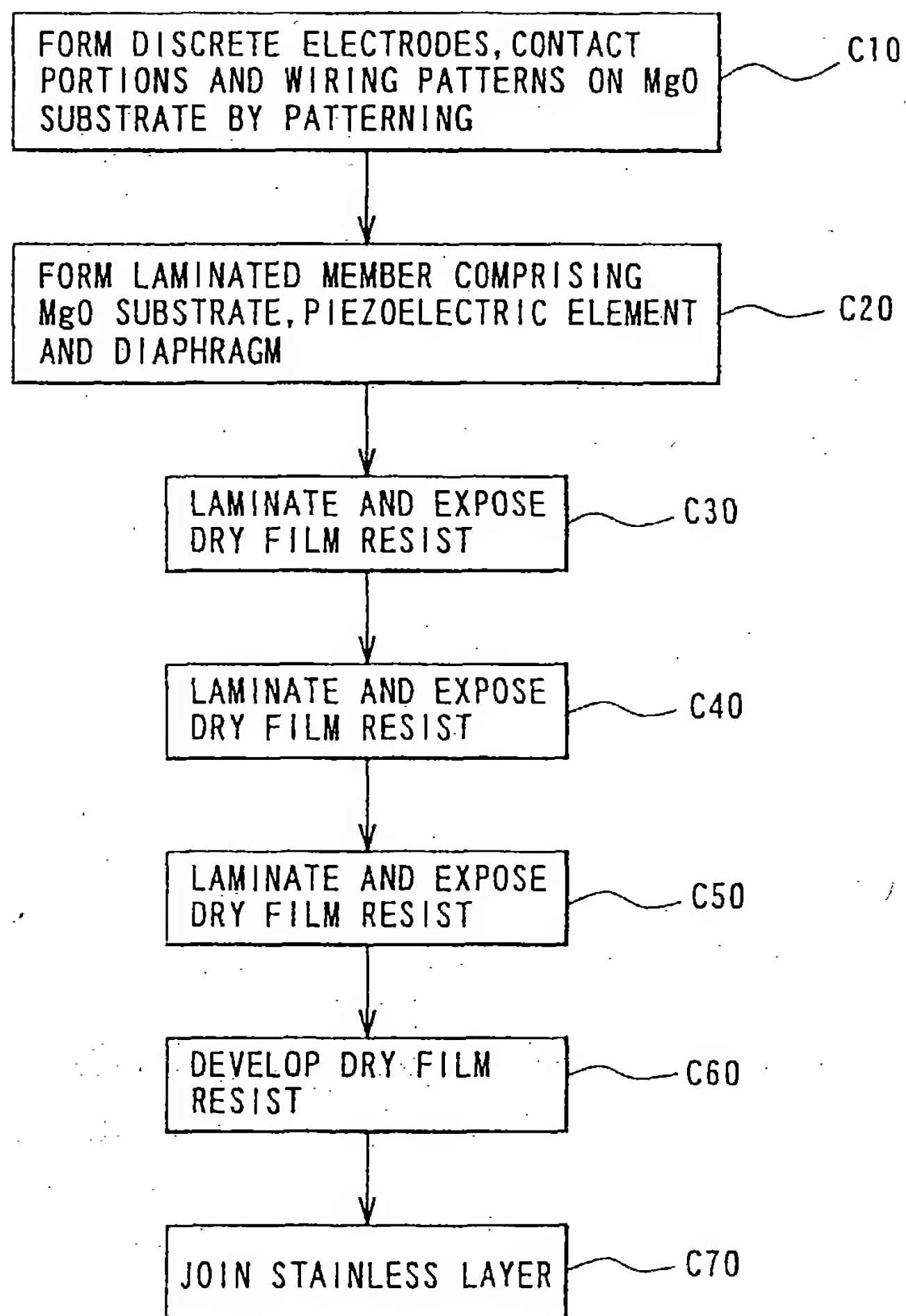
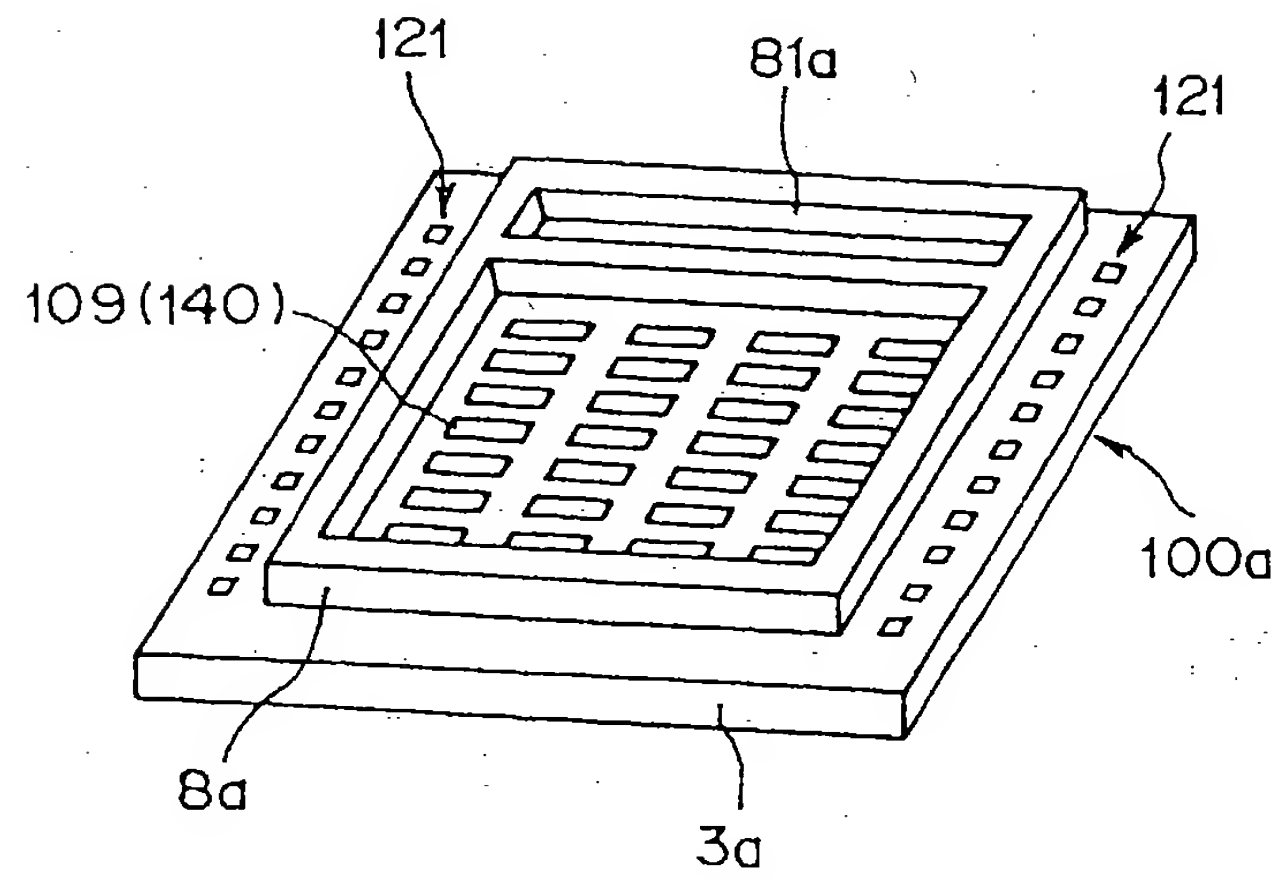


FIG. 14



# FIG. 15



# FIG. 16

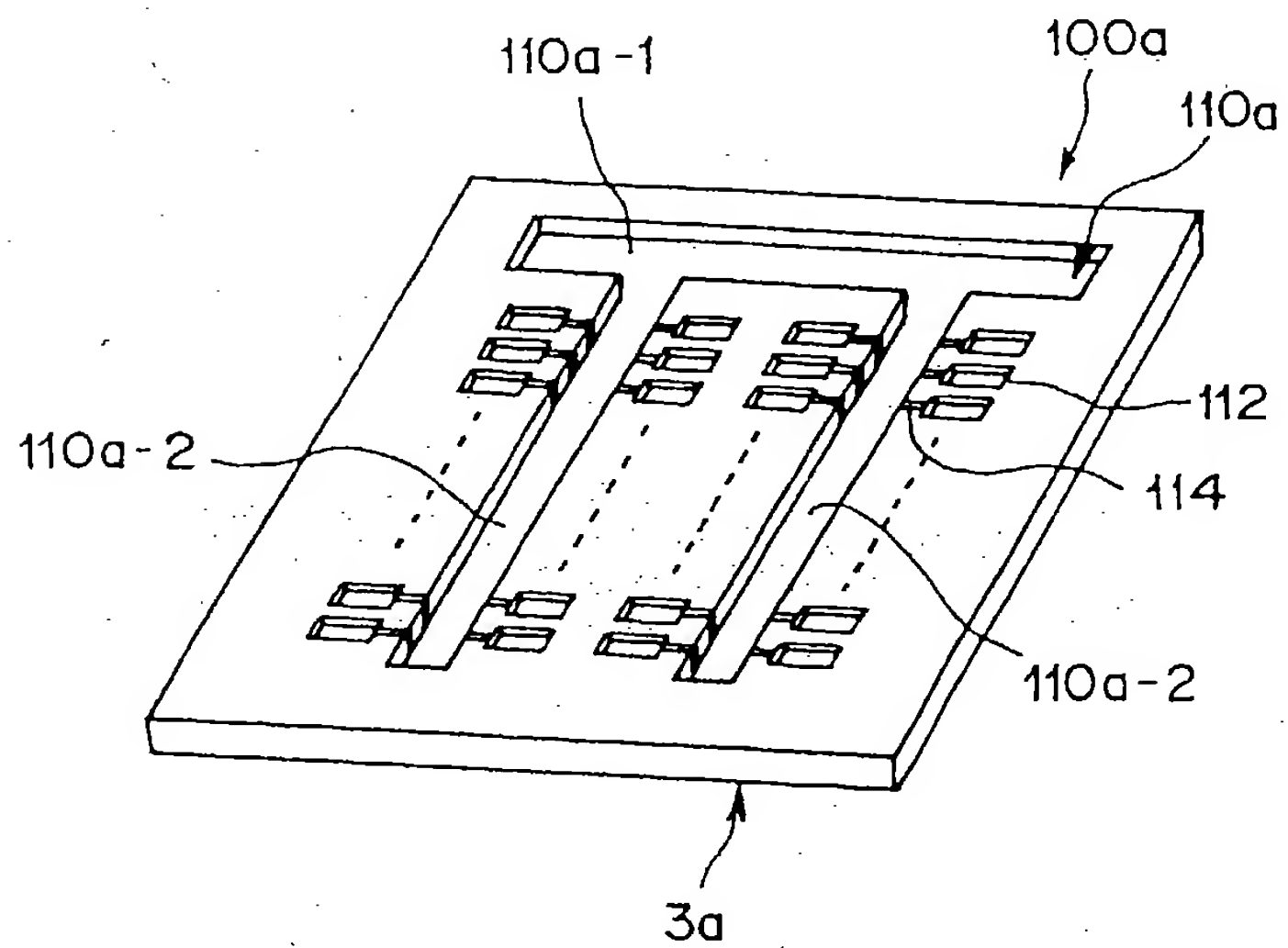


FIG. 17

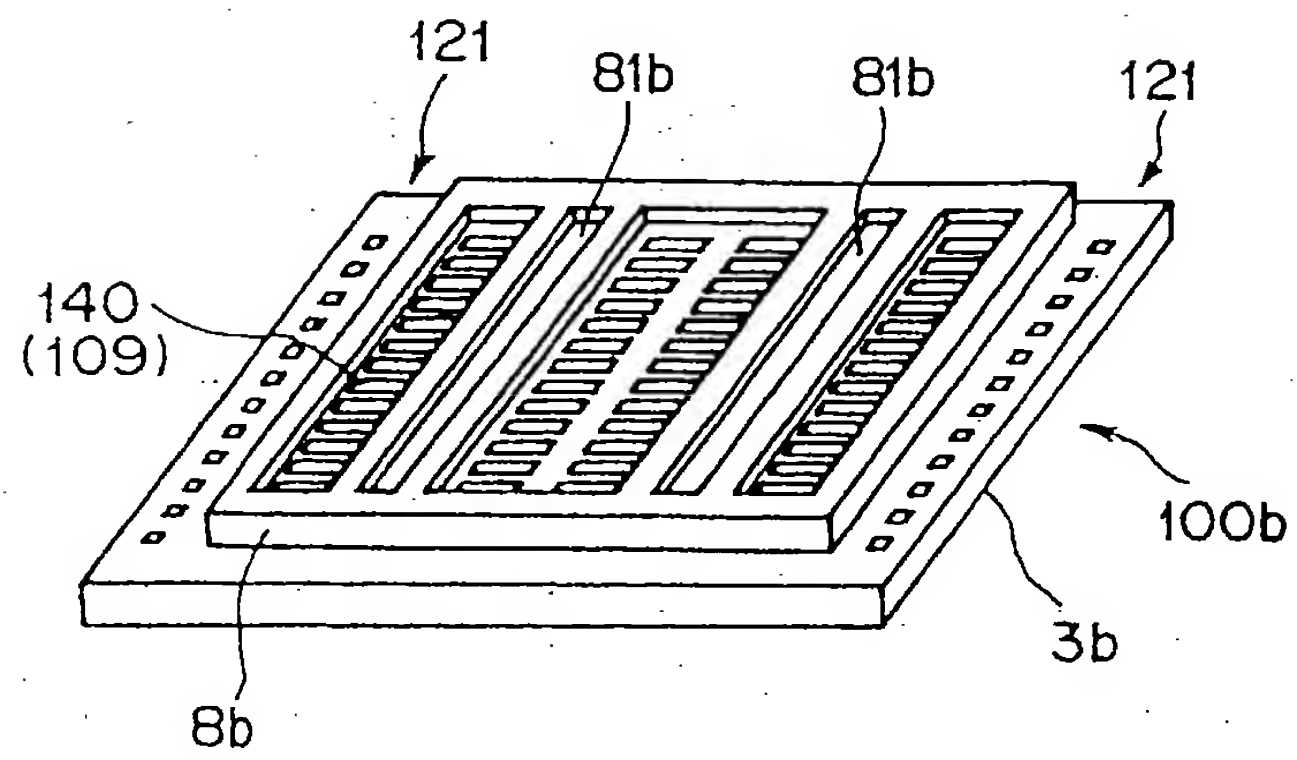
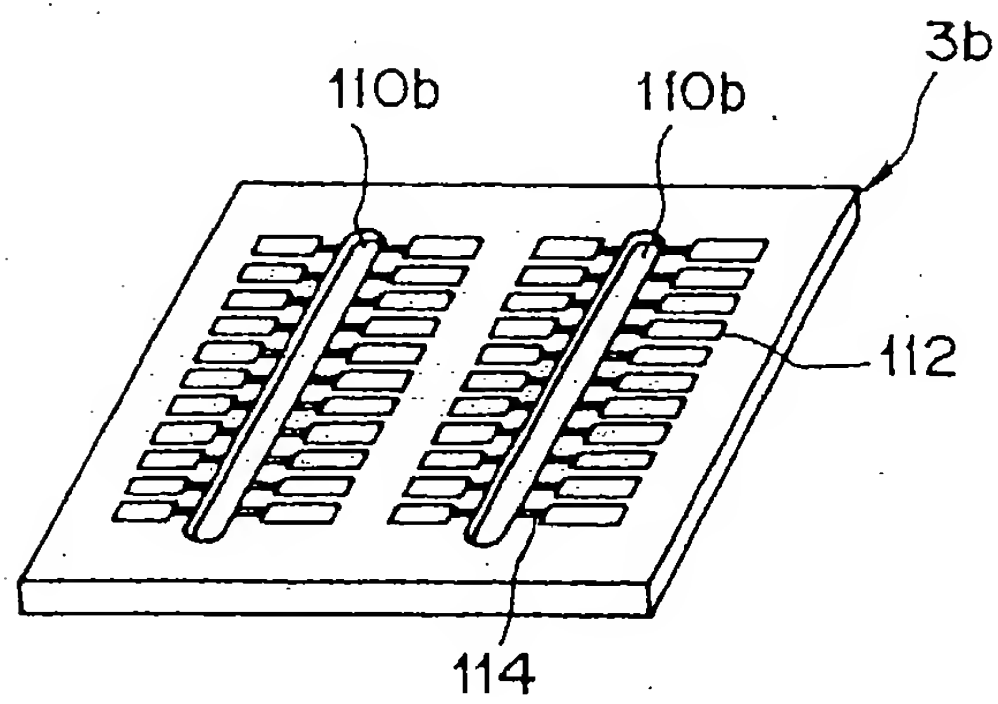
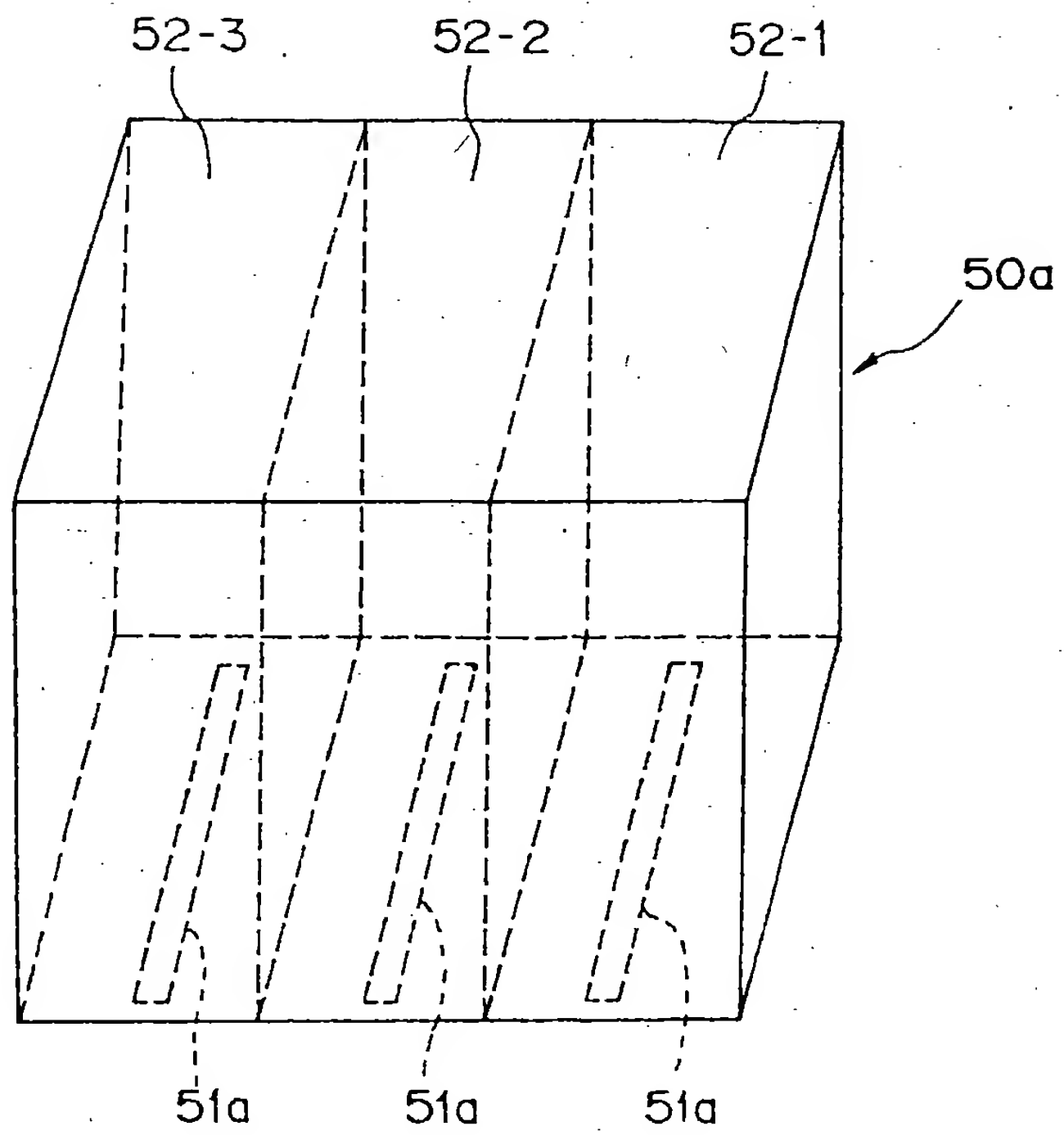


FIG. 18



# FIG. 19(a)



# FIG. 19(b)

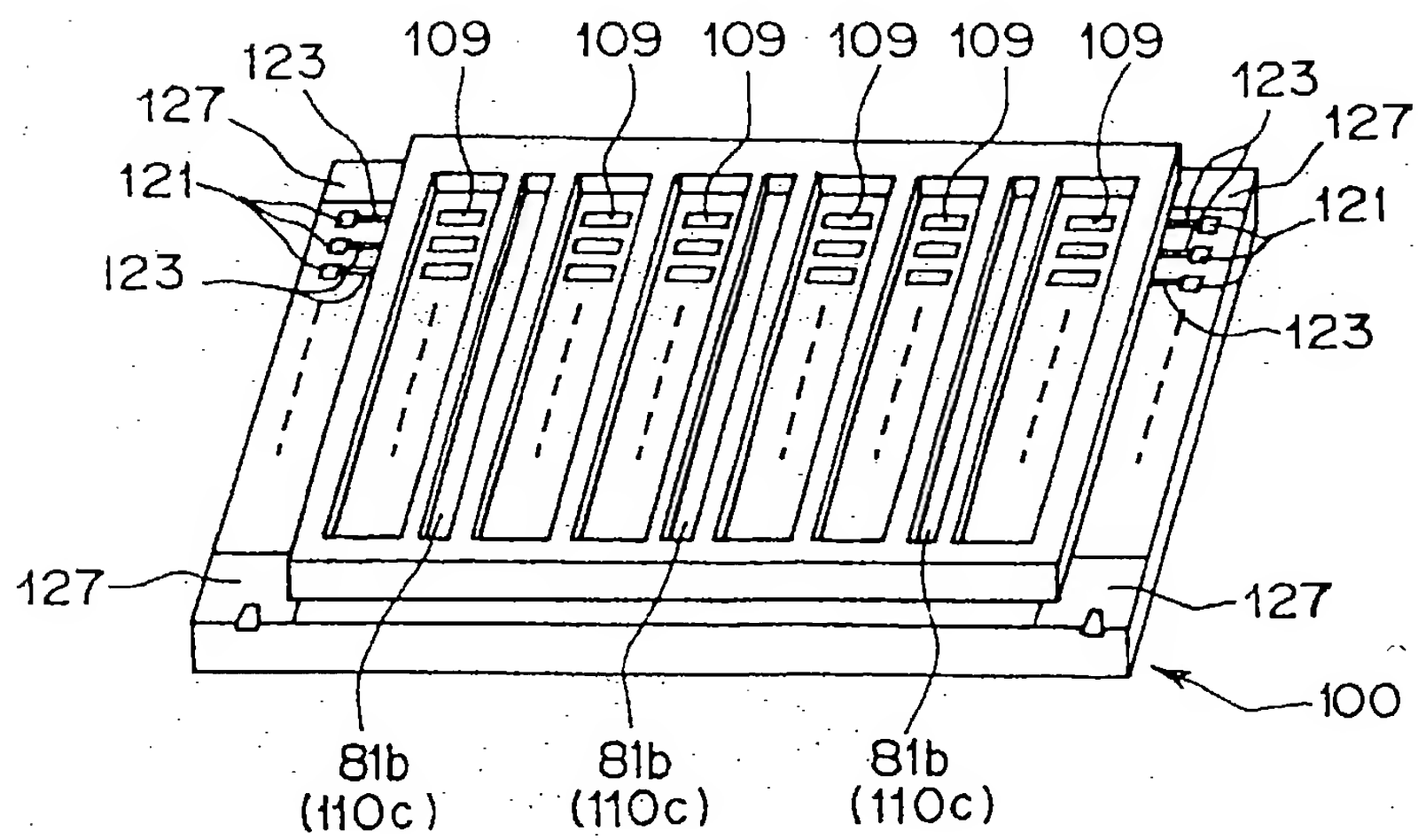


FIG. 20

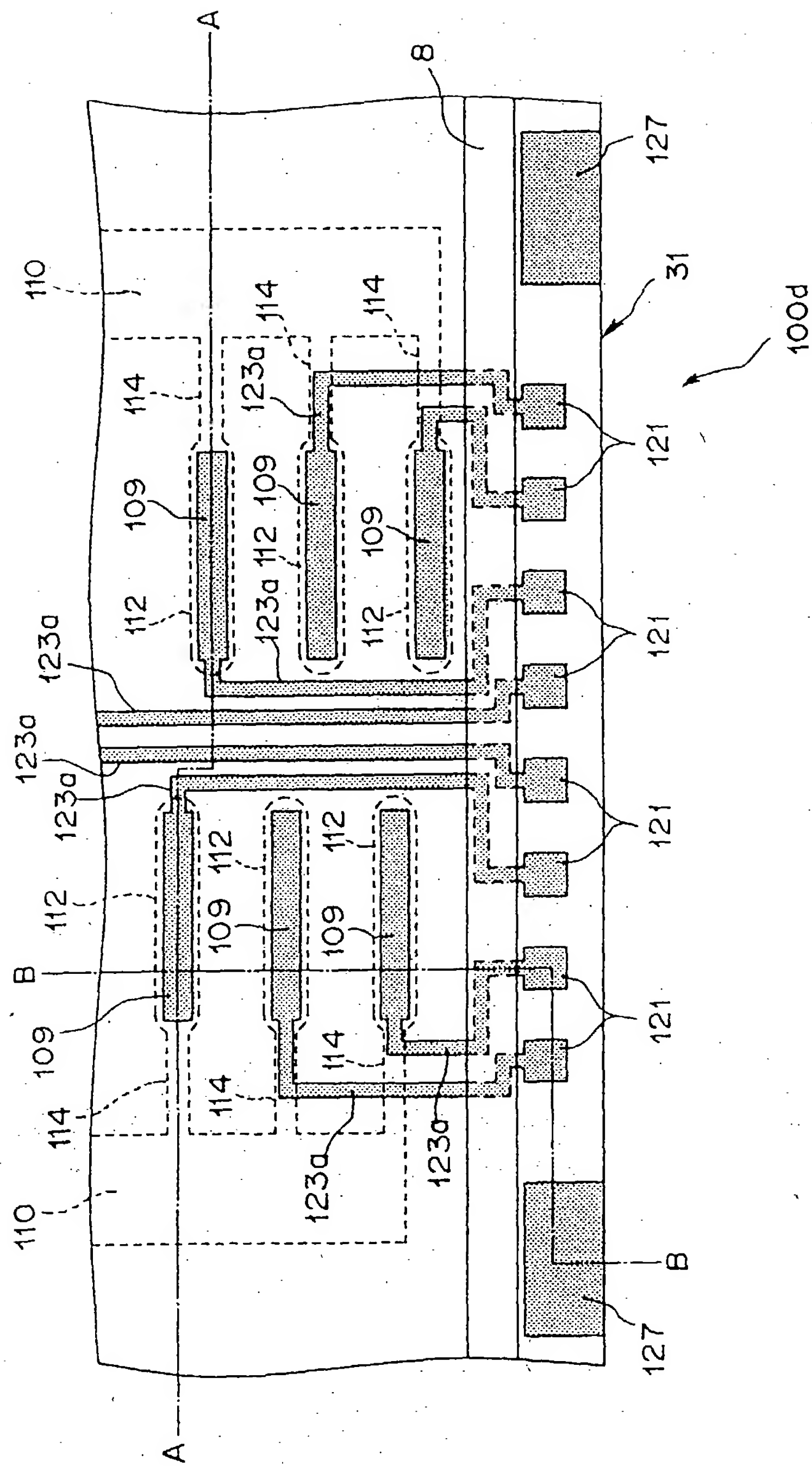




FIG. 21

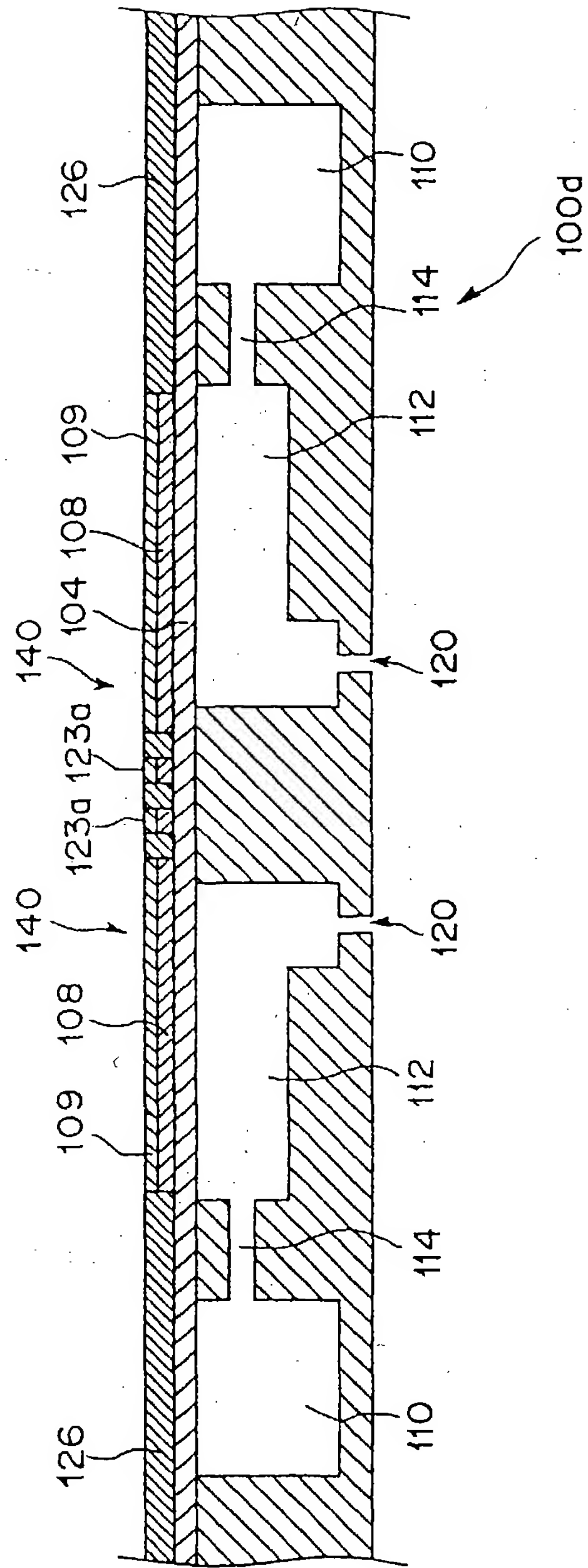




FIG. 23

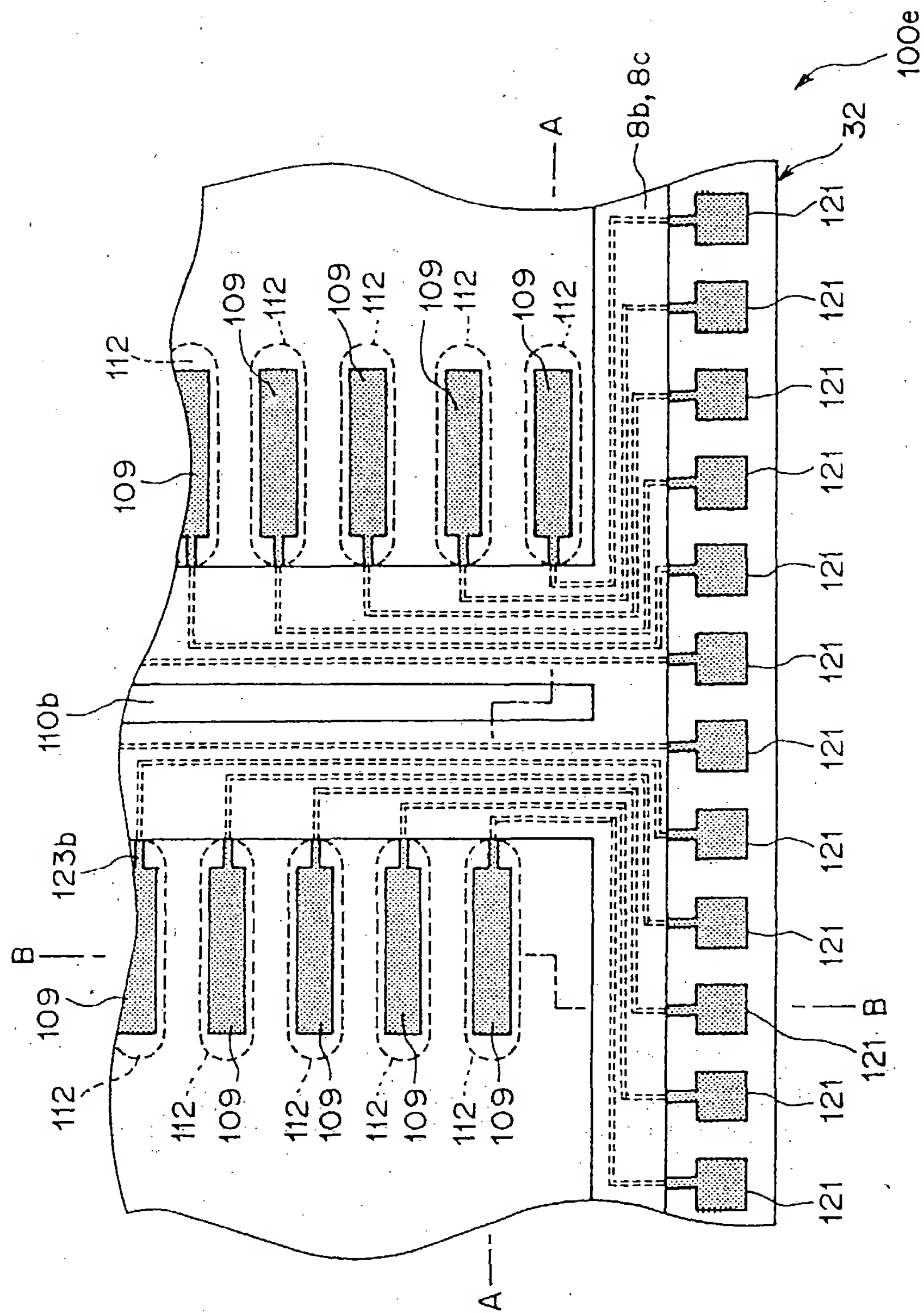




FIG. 25

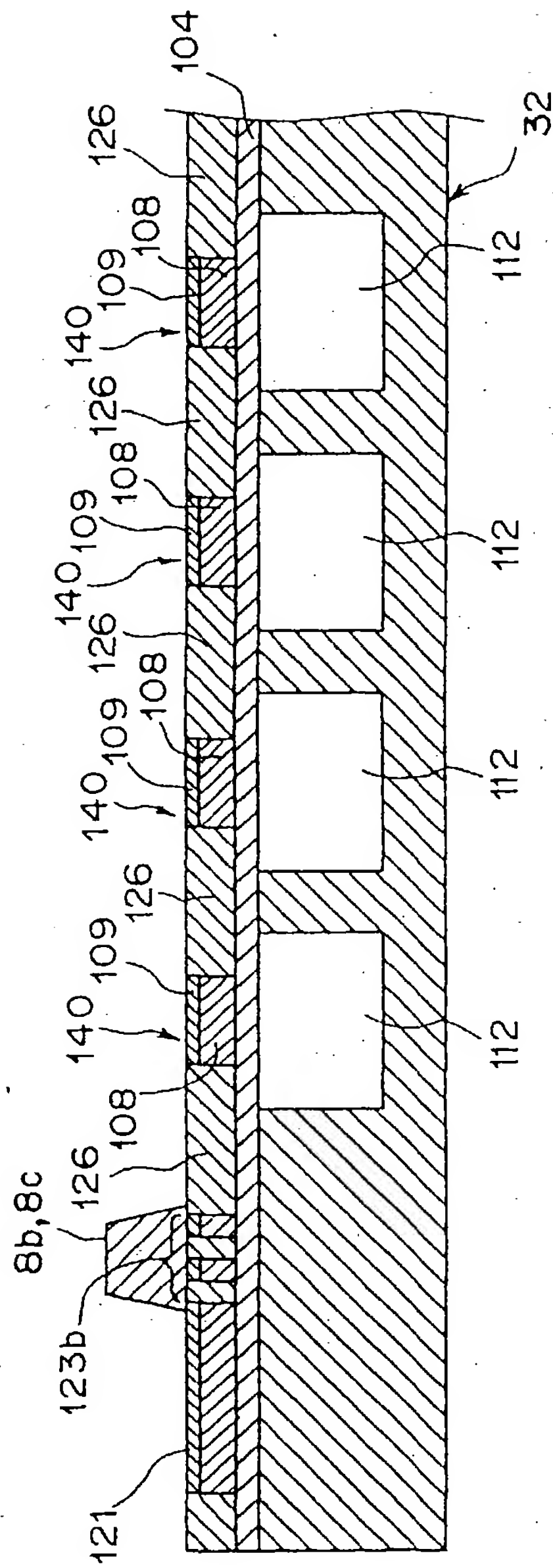


FIG. 26

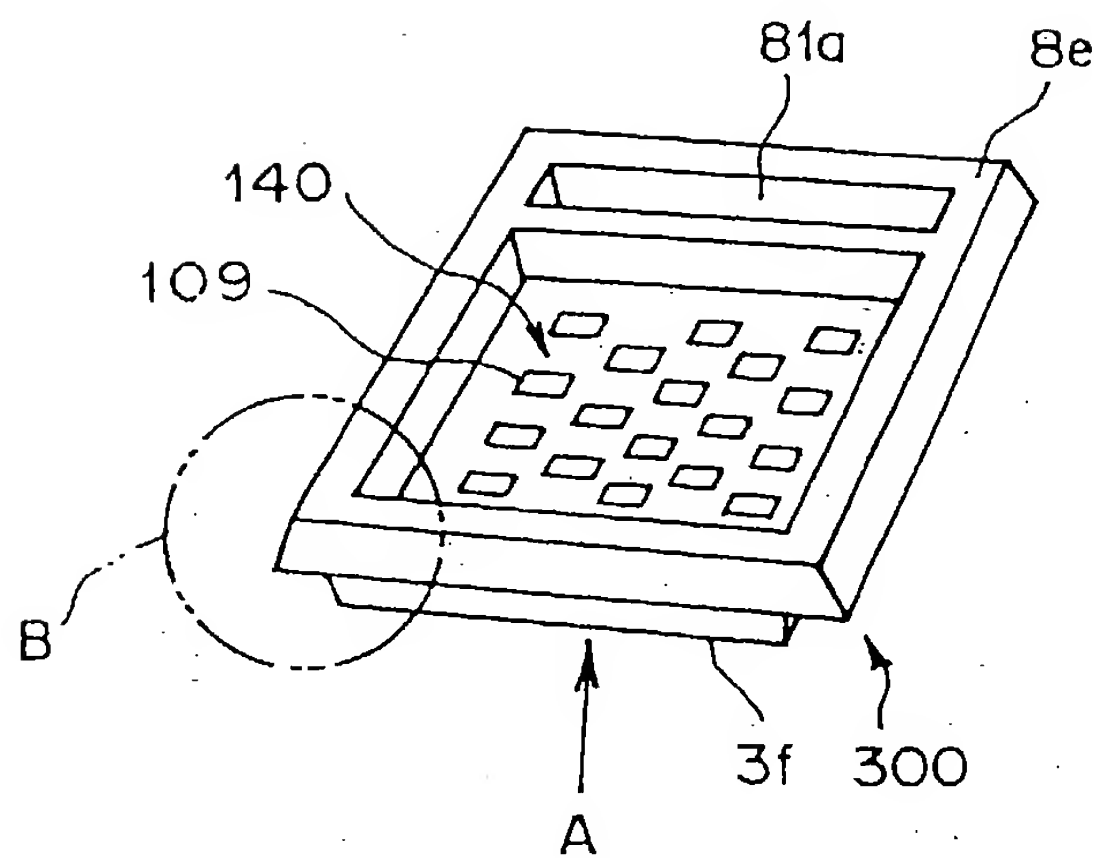
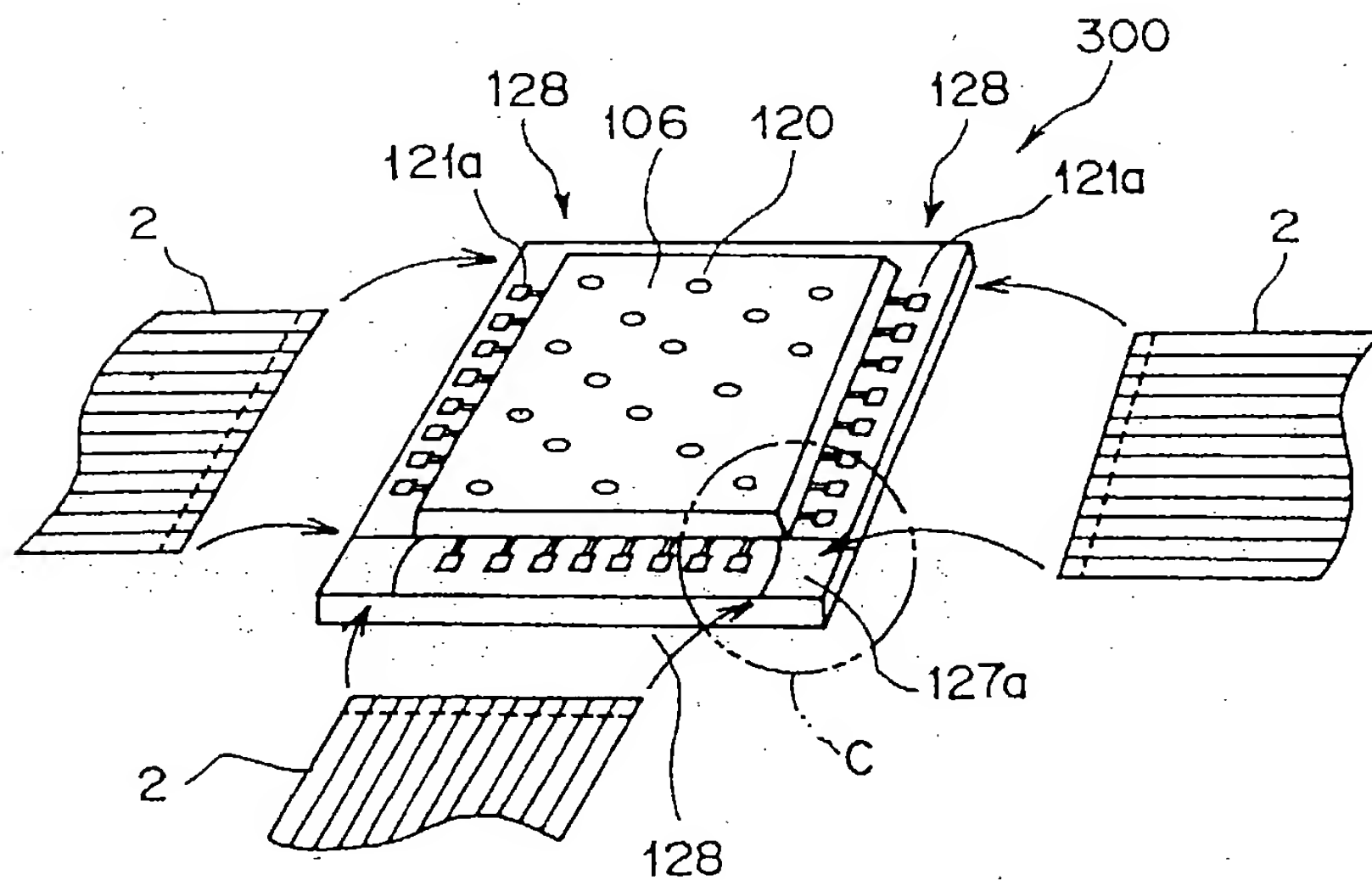
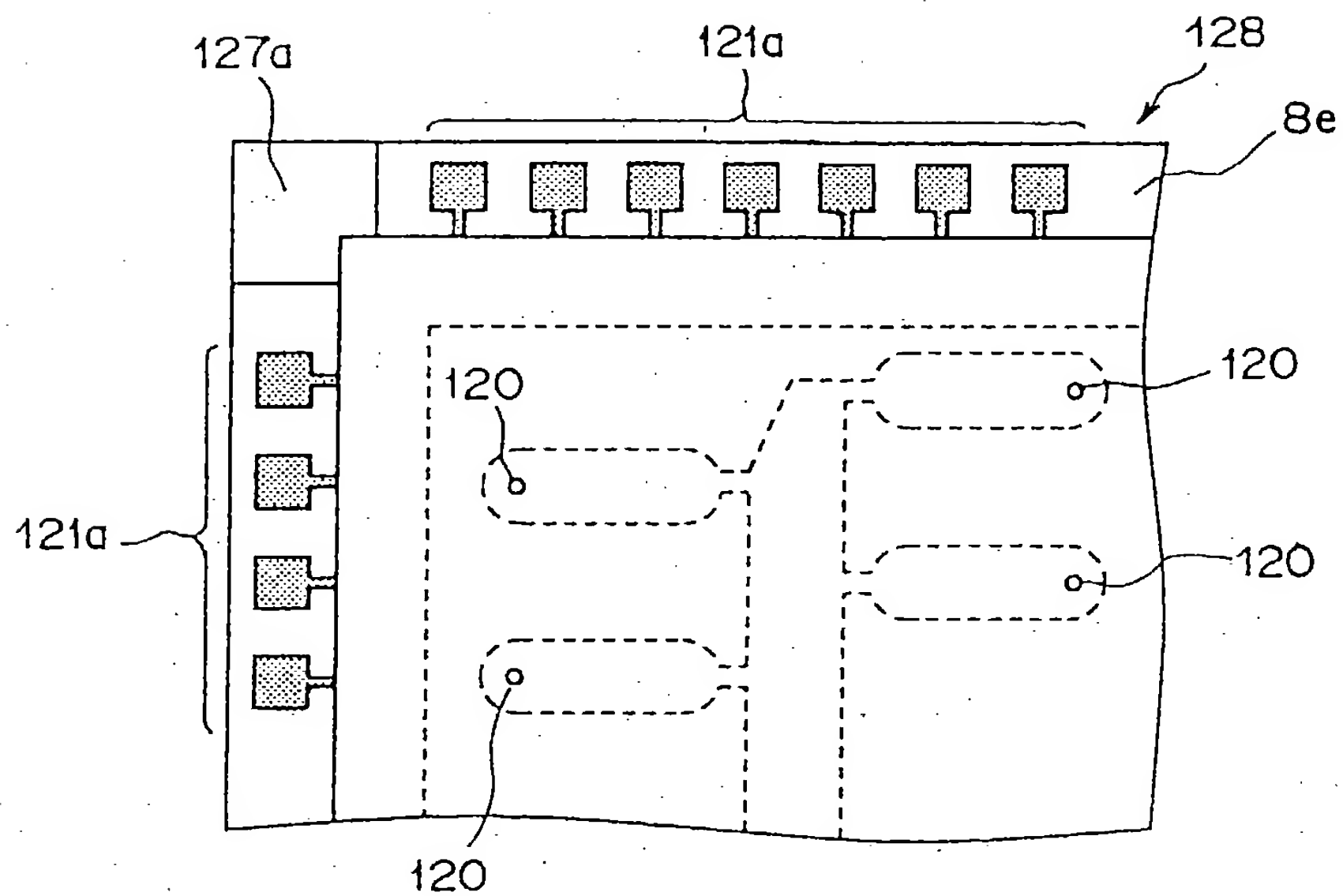


FIG. 27



This cross-sectional view shows a substrate 3f with a trench 120. A layer 128 is formed on the substrate, with a portion 121a on the left. A thin layer 104 is on top of 128. A layer 108 is on top of 104, with a portion 109 on the right. A structure 114 is formed in the trench 120. A structure 8e is on the left side of the device.

# FIG. 30



# FIG. 31

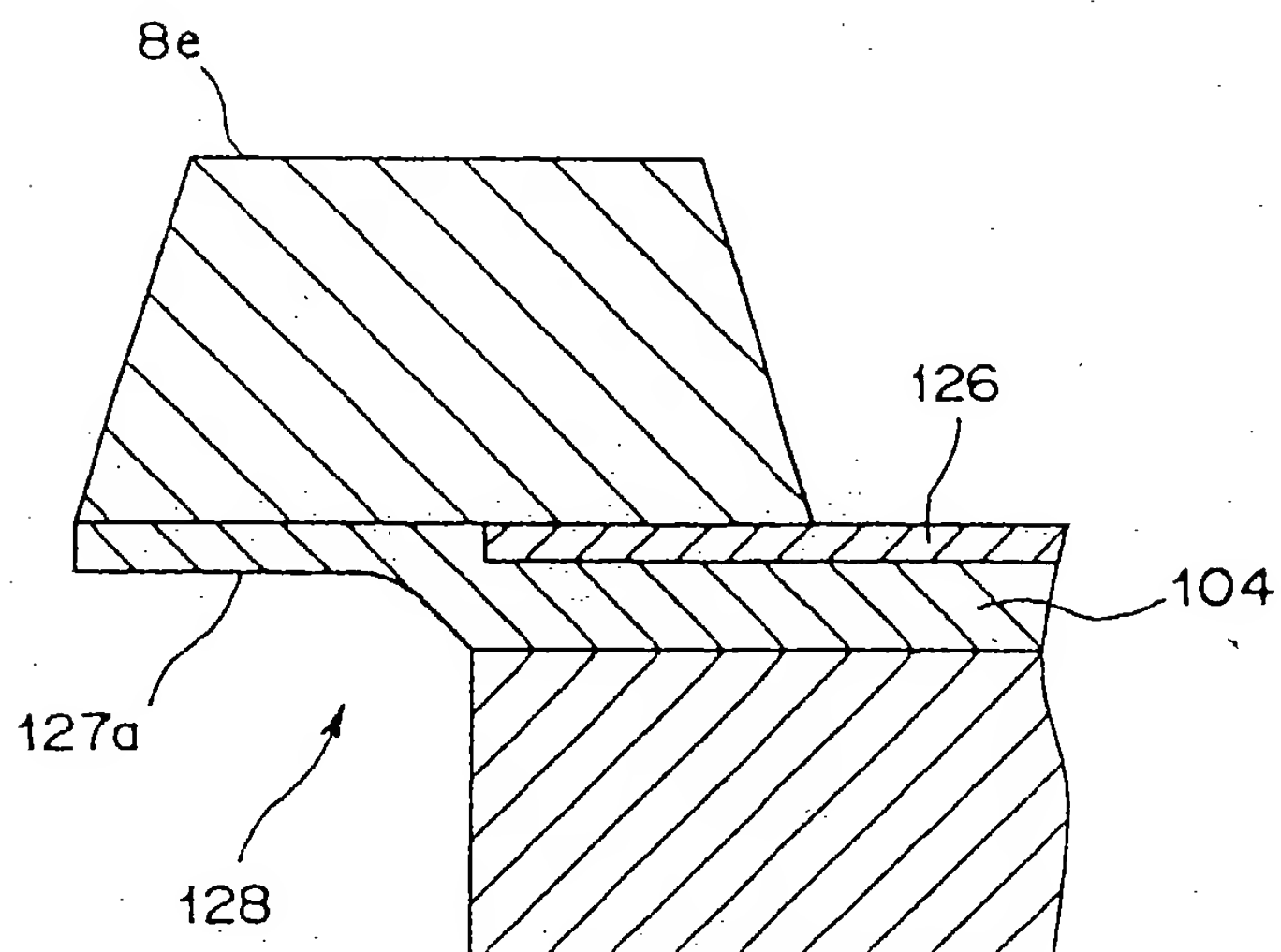




FIG. 32

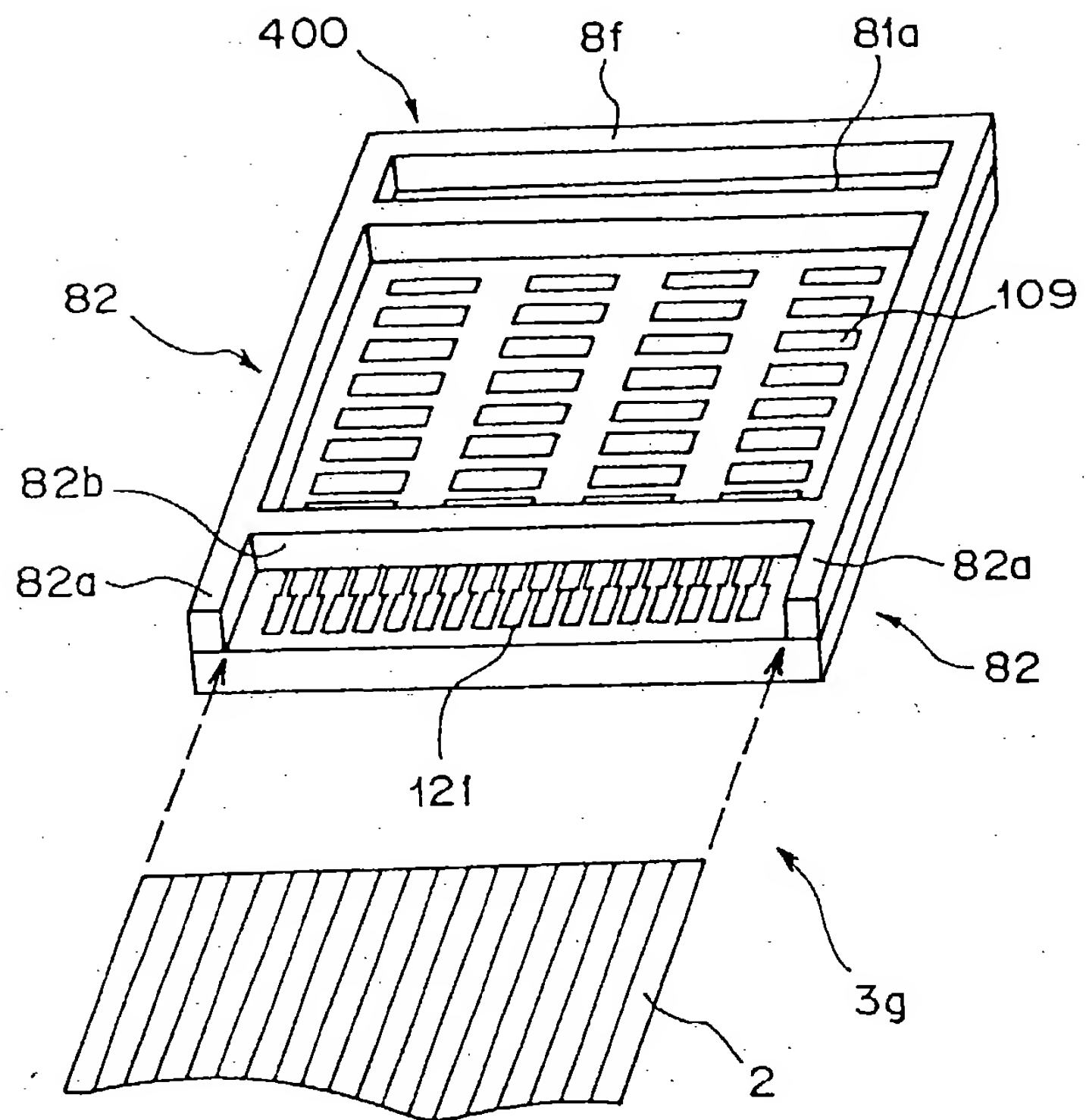


FIG. 33

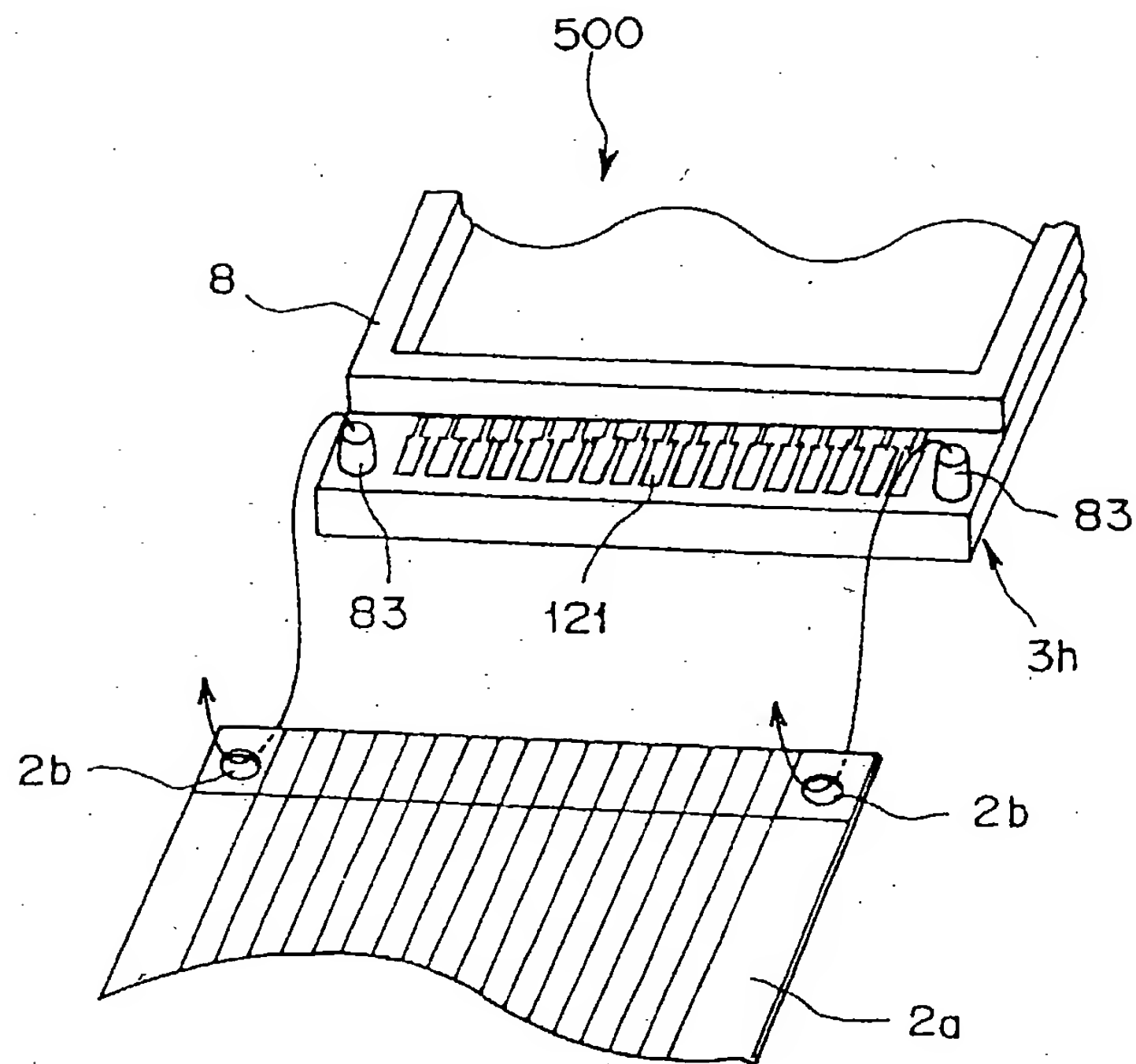


FIG. 34

